

AMENDMENTS TO THE SPECIFICATION

Please amend paragraph [0025] as follows:

[0025] Referring to FIG. 1A, the PEPSM 10 is formed of a quartz substrate 11 in which a trench 15 is formed. The trench 15 is formed by anisotropically etching a predetermined portion of the quartz substrate ~~[[10]]~~11. In the PEPSM 10, the region where the trench is formed is a 180° region, while the region of the quartz substrate 11 where the trench 15 is not formed is a 0° region.

Please amend paragraph [0090] as follows:

[0090] Referring first to FIG. 3A, a PEPSM 100 of the present invention includes a quartz substrate 105 having a trench 100. The trench 110 has such a depth as to shift the phase of incident light by 180°. Thus, a region where the trench 110 is formed is a 180° phase shift region (hereinafter, "180° region"), while the region of the quartz substrate 105 where the trench 110 is not formed is a 0° region. An auxiliary pattern is formed at predetermined portions of the 0° region and 180° region. The auxiliary pattern 120 may be formed on a planar surface as spaced laterally from the edge of the trench 110, for example, at the center of the 0° region and/or at the center of the bottom of the trench 110. The auxiliary pattern 120 may be formed of an optical interference material or an opaque material of, for example, chromium. Here, the line width and exposure conditions should be designed ~~for~~ so that the patterning of the photoresist will not occur at a region corresponding to the auxiliary pattern 120. In the present embodiment, the auxiliary pattern 120 is set to have a line width of 30 nm to 200 nm, for example.

Please amend paragraph [0095] as follows:

[0095] The optical characteristics of the PEPSM 100 of the present invention is shown in FIG. 3B. In FIG. 3B, curve B1 shows the optical intensity of the PEPSM before the auxiliary pattern 120 is formed, whereas curve B2 shows the optical intensity measured when the auxiliary pattern 120 is present. FIG. 3B thus shows that the presence of the auxiliary pattern 120 reduces the amplitude of the optical intensity provided by the PEPSM 100. This is because the auxiliary pattern 120 causes optical interference. A decrease in the optical intensity changes the slope of the intensity curve. Thus, the intervals between regions where the photoresist will be patterned, i.e., regions for example at region C in FIG. 3B corresponding to sidewalls of the trench, ~~[[is]]~~ are changed by the presence of the auxiliary pattern 120. Thus, the auxiliary pattern 120 can be used to provide a photoresist pattern of a desired line width.